

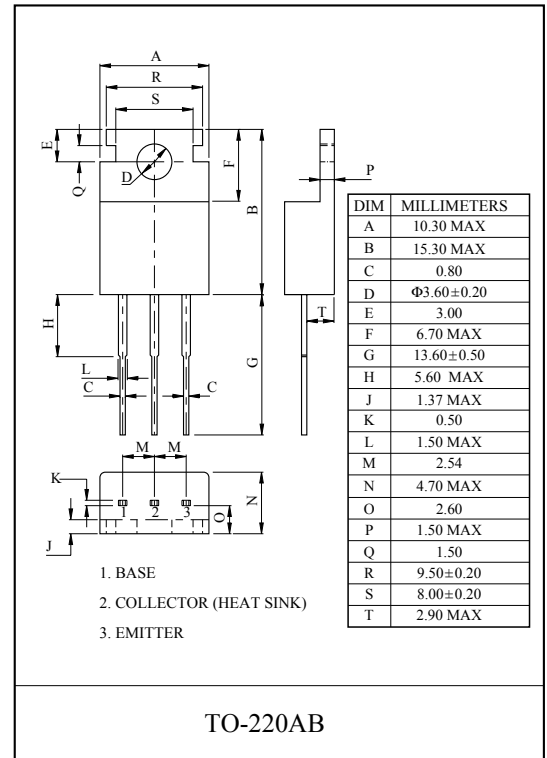
GENERAL PURPOSE APPLICATION.

FEATURES

- High Breakdown Voltage : $V_{CE0}=-100V$.
- Low Collector-Emitter Saturation Voltage.
: $V_{CE(sat)}=-2.0V(\text{Max.})$
- Complementary to KTD525.

MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-5	A
Emitter Current	I_E	5	A
Base Current	I_B	-0.5	A
Collector Power Dissipation (Tc=25°C)	P_C	40	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55 ~ 150	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=-100V, I_E=0$	-	-	-100	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=-5V, I_C=0$	-	-	-1.0	mA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-50mA, I_B=0$	-100	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-10mA, I_C=0$	-5.0	-	-	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE}=-5V, I_C=-1A$	40	-	240	
	$h_{FE(2)}$	$V_{CE}=-5V, I_C=-4A$	20	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-4A, I_B=-0.4A$	-	-	-2.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=-5V, I_C=-4A$	-	-	-1.5	V
Transition Frequency	f_T	$V_{CE}=-5V, I_C=-1A$	-	5.0	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$	-	270	-	pF

Note : $h_{FE(1)}$ Classification R:40 ~ 80 , O:70 ~ 140 , Y:120 ~ 240

